

Welcome to E-XFL.COM

What is "Embedded - Microcontrollers"?

"Embedded - Microcontrollers" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "<u>Embedded -</u> <u>Microcontrollers</u>"

Details

⊡XFI

Product Status	Not For New Designs
Core Processor	RL78
Core Size	16-Bit
Speed	20MHz
Connectivity	CSI, I ² C, LINbus, UART/USART
Peripherals	DMA, LVD, POR, PWM, WDT
Number of I/O	6
Program Memory Size	1KB (1K x 8)
Program Memory Type	FLASH
EEPROM Size	-
RAM Size	128 x 8
Voltage - Supply (Vcc/Vdd)	2V ~ 5.5V
Data Converters	A/D 4x8/10b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	10-LSSOP (0.173", 4.40mm Width)
Supplier Device Package	10-LSSOP
Purchase URL	https://www.e-xfl.com/product-detail/renesas-electronics-america/r5f10y14asp-v0

Email: info@E-XFL.COM

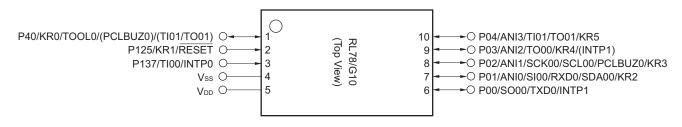
Address: Room A, 16/F, Full Win Commercial Centre, 573 Nathan Road, Mongkok, Hong Kong

- Note For the fields of application, refer to Figure 1-1 Part Number, Memory Size, and Package of RL78/G10.
- Caution The part number represents the number at the time of publication. Be sure to review the latest part number through the target product page in the Renesas Electronics Corp.website.

<R> 1.3 Pin Configuration (Top View)

1.3.1 10-pin products

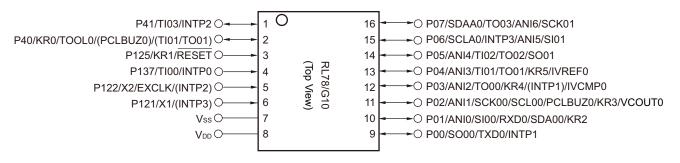
• 10-pin plastic LSSOP (4.4 × 3.6 mm, 0.65 mm pitch)



- Remarks 1. For pin identification, see 1.4 Pin Identification.
 - Functions in parentheses in the above figure can be assigned via settings in the peripheral I/O redirection register (PIOR). See Figure 4-6 Format of Peripheral I/O Redirection Register (PIOR) in the RL78/G10 User's Manual.

1.3.2 16-pin products

• 16-pin plastic SSOP (4.4 × 5.0 mm, 0.65 mm pitch)

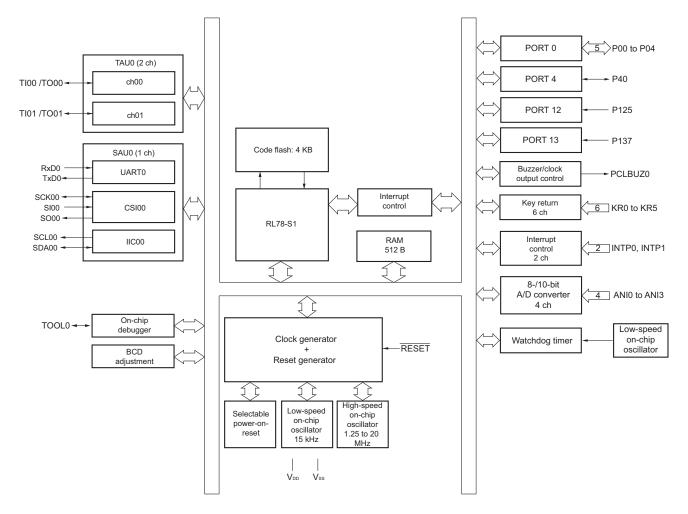


- Remarks 1. For pin identification, see 1.4 Pin Identification.
 - Functions in parentheses in the above figure can be assigned via settings in the peripheral I/O redirection register (PIOR). See Figure 4-6 Format of Peripheral I/O Redirection Register (PIOR) in the RL78/G10 User's Manual.



1.5 Block Diagram

1.5.1 10-pin products





1.6 Outline of Functions

This outline describes the function at the time when Peripheral I/O redirection register (PIOR) is set to 00H.

	Item		10-pin			16-pin		
		R5F10Y14	R5F10Y16	R5F10Y17	R5F10Y44	R5F10Y46	R5F10Y47	
Code flash	memory	1 KB	2 KB	4 KB	1 KB	2 KB	4 KB	
RAM		128 B	256 B	512 B	128 B	256 B	512 B	
Main system clock	High-speed system clock	_			main system of 1 to 20 MHz: 1	al/ceramic) oscilla clock input (EXCL VDD = 2.7 to 5.5 V DD = 2.0 to 5.5 V	K): /	
	High-speed on-chip	• 1.25 to 20	MHz (Vdd = 2.7	to 5.5 V)				
	oscillator clock		1Hz (Vod = 2.0 to	,				
Low-speed clock	on-chip oscillator	15 kHz (TYP)						
	urpose register	8-bit register	× 8					
	nstruction execution		/Hz operation)					
Instruction	set	MultiplicationRotate, bar	subtractor/logication (8 bits \times 8 bits rrel shift, and bit					
I/O port	Total	8	,		14			
	CMOS I/O	6 (N-ch open	-drain output (Vi	op tolerance): 2)	10 (N-ch oper	n-drain output (VD	D tolerance): 4	
	CMOS input	2		, , ,	4	• •	,	
Timer	16-bit timer	2 channels			4 channels			
	Watchdog timer	1 channel						
	12-bit interval timer	_			1 channel			
	Timer output	2 channels (F	PWM output: 1)		4 channels (P	WM outputs: 3 No	^{te 1})	
Clock outp	ut/buzzer output	1			•			
		2.44 kHz to 1	0 MHz: (Periphe	eral hardware cloo	ck: fmain = 20 MHz	operation)		
Comparate	or	—			1			
8-/10-bit re	esolution A/D converter	4 channels			7 channels			
Serial inte	face	[10-pin produ	icts] CSI: 1 chan	nel/simplified I ² C	: 1 channel/UART	: 1 channel		
		[16-pin produ	icts] CSI: 2 chan	nels/simplified I20	C: 1 channel/UAR	T: 1 channel		
	I ² C bus	—			1 channel			
Vectored	Internal	8			14			
interrupt sources	External	3			5			
Key interru	ıpt	6						
Reset		Reset by R	RESET pin					
		Internal reset by watchdog timer						
		Internal reset by selectable power-on-reset						
		Internal reset by illegal instruction execution Note 2						
				tion lower limit vo	oltage			
Selectable	power-on-reset circuit	Detection v	-					
				//2.68 V/3.02 V/4.				
		Falling edge (V _{SPDR}): 2.20 V/2.62 V/2.96 V/4.37 V (max.)						



2. ELECTRICAL SPECIFICATIONS

- Cautions 1. The RL78 microcontrollers have an on-chip debug function, which is provided for development and evaluation. Do not use the on-chip debug function in products designated for mass production, because the guaranteed number of rewritable times of the flash memory may be exceeded when this function is used, and product reliability therefore cannot be guaranteed. Renesas Electronics is not liable for problems occurring when the on-chip debug function is used.
 - 2. The pins mounted depend on the product. Refer to 2.1 Port Functions and 2.2.1 Functions for each product in the RL78/G10 User's Manual.
 - 3. Use this product within the voltage range from 2.25 to 5.5 V because the detection voltage (VSPOR) of the selectable power-on-reset (SPOR) circuit should also be considered.



2.2 Oscillator Characteristics

2.2.1 X1 oscillator characteristics

 $(T_A = -40 \text{ to } +85^{\circ}\text{C}, 2.0 \text{ V} \le \text{V}_{DD} \le 5.5 \text{ V}, \text{V}_{SS} = 0 \text{ V})$

Parameter	Resonator	Conditions	MIN.	TYP.	MAX.	Unit
X1 clock	Ceramic resonator/	$2.7~V \leq V_{\text{DD}} \leq 5.5~V$	1		20	MHz
oscillation frequency (fx) ^{Note}	crystal resonator	$2.0 \text{ V} \le \text{V}_{\text{DD}} < 2.7 \text{ V}$	1		5	MHz

- **Note** Indicates only permissible oscillator frequency ranges. Refer to AC Characteristics for instruction execution time. Request evaluation by the manufacturer of the oscillator circuit mounted on a board to check the oscillator characteristics.
- Caution Since the CPU is started by the high-speed on-chip oscillator clock after a reset release, check the X1 clock oscillation stabilization time using the oscillation stabilization time counter status register (OSTC) by the user. Determine the oscillation stabilization time of the OSTC register and the oscillation stabilization time select register (OSTS) after sufficiently evaluating the oscillation stabilization time with the resonator to be used.
- Remark When using the X1 oscillator, refer to 5.4 System Clock Oscillator in the RL78/G10 User's Manual.

2.2.2 On-chip oscillator characteristics

$(1A = -40 \ 10 \ 403 \ 0, \ 2.0 \ V \le V DD \le 3.3)$						
Oscillators	Parameters	Conditions	MIN.	TYP.	MAX.	Unit
High-speed on-chip oscillator oscillation clock frequency Notes 1, 2	fін		1.25		20	MHz
High-speed on-chip oscillator oscillation		TA = -20 to +85°C	-2.0		+2.0	%
clock frequency accuracy		TA = -40 to -20°C	-3.0		+3.0	%
Low-speed on-chip oscillator oscillation clock frequency	fı∟			15		kHz
Low-speed on-chip oscillator oscillation clock frequency accuracy			-15		+15	%

Notes 1. High-speed on-chip oscillator frequency is selected by bits 0 to 2 of option byte (000C2H).

2. This only indicates the oscillator characteristics. Refer to AC Characteristics for instruction execution time.



(1/2)

2.3 DC Characteristics

2.3.1 Pin characteristics

$(T_A = -40 \text{ to } +85^{\circ}\text{C}, 2.0 \text{ V} \le \text{V}_{DD} \le 5.5 \text{ V}, \text{V}_{SS} = 0 \text{ V})$

TA = -40 10 + 65 C,	2.0 V 5	$VDD \leq 5.5 V, Vss = 0 V)$					(1/2)
Parameter	Symbol	Conditions		MIN.	TYP.	MAX.	Unit
Output current, high Note 1	Іон1	Per pin for 10-pin products: P00 to P04, P40 16-pin products: P00 to P07, P40, P41				-10.0 Note 2	mA
		Total of 10-pin products: P40 16-pin products: P40, P41	$\begin{array}{c} 4.0 \ V \leq V_{DD} \leq 5.5 \ V \\ \hline 2.7 \ V \leq V_{DD} < 4.0 \ V \\ \hline 2.0 \ V \leq V_{DD} < 2.7 \ V \end{array}$			-20.0 -4.0 -3.0	mA mA mA
		(When duty ≤ 70% ^{Note 3}) Total of 10-pin products: P00 to P04	$4.0 V \le V_{DD} \le 5.5 V$ $2.7 V \le V_{DD} < 4.0 V$			-60.0 -12.0	mA
		16-pin products: P00 to P07 (When duty \leq 70% ^{Note 3})	$2.0~V \leq V_{\text{DD}} < 2.7~V$			-9.0	mA
Output current, low Note 4	IOL1	Total of all pins (When duty ≤ 70% ^{Note 3}) Per pin for 10-pin products: P00 to P04, P40 16-pin products: P00 to P07, P40, P41				-80.0 20.0 Note 2	mA mA
	4 10- 16- Tot 10- 10- 16-	Total of 10-pin products: P40 16-pin products: P40, P41 (When duty ≤ 70% ^{Note 3})				40.0 6.0 1.2	mA mA mA
		Total of 10-pin products: P00 to P04 16-pin products: P00 to P07 (When duty \leq 70% ^{Note 3})	$\begin{array}{l} 4.0 \ V \leq V_{DD} \leq 5.5 \ V \\ \hline 2.7 \ V \leq V_{DD} < 4.0 \ V \\ \hline 2.0 \ V \leq V_{DD} < 2.7 \ V \end{array}$			80.0 12.0 2.4	mA mA mA
		Total of all pins (When duty $\leq 70\%$ ^{Note 3})				120.0	mA

Notes 1. Value of current at which the device operation is guaranteed even if the current flows from the V_{DD} pin to an output pin.

- 2. Do not exceed the total current value.
- 3. This is the output current value under conditions where the duty factor ≤ 70%. The output current value when the duty factor > 70% can be calculated with the following expression (when changing the duty factor to n%).
 - Total output current of pins = (I_{OH} × 0.7)/(n × 0.01)
 <Example> Where n = 80 % and I_{OH} = 10.0 mA
 Total output current of pins = (- 10.0 × 0.7)/(80 × 0.01) ≅ 8.7 mA
 - Total output current of pins = (IoL × 0.7)/(n × 0.01) <Example> Where n = 80 % and IoL = 10.0 mA

Total output current of pins = $(10.0 \times 0.7)/(80 \times 0.01) \approx 8.7 \text{ mA}$

However, the current that is allowed to flow into one pin does not vary depending on the duty factor. A current higher than the absolute maximum rating must not flow into one pin.

4. Value of current at which the device operation is guaranteed even if the current flows from an output pin to the Vss pin.

Caution P00, P01, P06, and P07 do not output high level in N-ch open-drain mode.

Remark Unless specified otherwise, the characteristics of alternate-function pins are the same as those of the port.

(2/2)

T _A = −40 to +85°C,	2.0 V ≤ `	$V_{DD} \leq 5.5 V, V_{SS} = 0 V$						
Parameter	Symbol	Condition	S	MIN.	TYP.	MAX.	Unit	
Input voltage, high	VIH1			0.8 VDD		Vdd	V	
Input voltage, low	VIL1			0		0.2 VDD	V	
Output voltage, high	Voh1	$4.0~V \leq V_{\text{DD}} \leq 5.5~V$	Iон = -10 mA	Vdd - 1.5			V	
Note 1			Iон = -3.0 mA	Vdd - 0.7			V	
		$\begin{array}{c c c c c c c c c c c c c c c c c c c $		V				
		$2.0~V \leq V_{\text{DD}} \leq 5.5~V$	Іон = -1.5 mA	Vdd - 0.5			V	
Output voltage, low	Vol1	$4.0~V \leq V_{\text{DD}} \leq 5.5~V$	IoL = 20 mA			1.3	V	
Note 2			lo∟ = 8.5 mA			0.7	V	
		$2.7~V \le V_{\text{DD}} \le 5.5~V$	IoL = 3.0 mA			0.6	V	
			lo∟ = 1.5 mA			0.4	V	
		$2.0~V \leq V_{\text{DD}} \leq 5.5~V$	IoL = 0.6 mA			0.4	V	
Input leakage	Ілні	P00 to P07, P40, P41, P125, P137				1	μA	
current, high		$V_{I} = V_{DD}$						
	ILIH2	P121, P122 (X1, X2, EXCLK)	In input port or			1		
		$V_{I} = V_{DD}$	external clock input					
			In resonator			10		
			connection					
Input leakage	ILIL1	P00 to P07, P40, P41, P125, P137	·			-1	μA	
current, low		$V_1 = V_{SS}$						
	ILIL2	P121, P122 (X1, X2, EXCLK)	In input port or			-1		
		$V_1 = V_{SS}$	external clock input					
			In resonator			-10		
			connection					
On-chip pull-up resistance	Ru	Vi = Vss		10	20	100	kΩ	

$(T_A = -40 \text{ to } +85^{\circ}\text{C}, 2.0 \text{ V} \le \text{V}_{DD} \le 5.5 \text{ V}, \text{ V}_{SS} = 0 \text{ V})$

Notes 1. The value under the condition which satisfies the high-level output current (IOH1).

2. The value under the condition which satisfies the low-level output current (IoL1).

- Caution The maximum value of VIH of P00, P01, P06, and P07 is VDD even in N-ch open-drain mode. P00, P01, P06, and P07 do not output high level in N-ch open-drain mode.
- Remark Unless specified otherwise, the characteristics of alternate-function pins are the same as those of the port.



2.3.2 Supply current characteristics

(1) Flash ROM: 1 and 2 KB of 10-pin products

$(T_A = -40 \text{ to } +85^{\circ}\text{C}, 2.0 \text{ V} \le \text{V}_{DD} \le 5.5 \text{ V}, \text{ Vss} = 0 \text{ V})$

Parameter	Symbol			Conditions		MIN.	TYP.	MAX.	Unit
Supply current	Idd1	Operating mode	Basic operation	f⊪ = 20 MHz	V _{DD} = 3.0 V, 5.0 V		0.91		mA
			Normal	f _{IH} = 20 MHz	V _{DD} = 3.0 V, 5.0 V		1.57	2.04	
			operation	f⊪ = 5 MHz	V _{DD} = 3.0 V, 5.0 V		0.85	1.15	
	DD2 ^{Note 2}	HALT mode		fiH = 20 MHz	V _{DD} = 3.0 V, 5.0 V		350	820	μA
				fін = 5 MHz	V _{DD} = 3.0 V, 5.0 V		290	600	
	DD3 ^{Note 3}	STOP mode	Э	V _{DD} = 3.0 V	•		0.56	2.00	μA

Notes 1. Total current flowing into V_{DD}, including the input leakage current flowing when the level of the input pin is fixed to V_{DD} or V_{SS}. The values below the MAX. column include the peripheral operation current. However, not including the current flowing into the A/D converter, I/O port, and on-chip pull-up/pull-down resistors.

- 2. During HALT instruction execution by flash memory.
- 3. Not including the current flowing into the watchdog timer.
- Remarks 1. fin: High-speed on-chip oscillator clock frequency
 - **2.** Temperature condition of the typical value is $T_A = 25^{\circ}C$



2.4 AC Characteristics

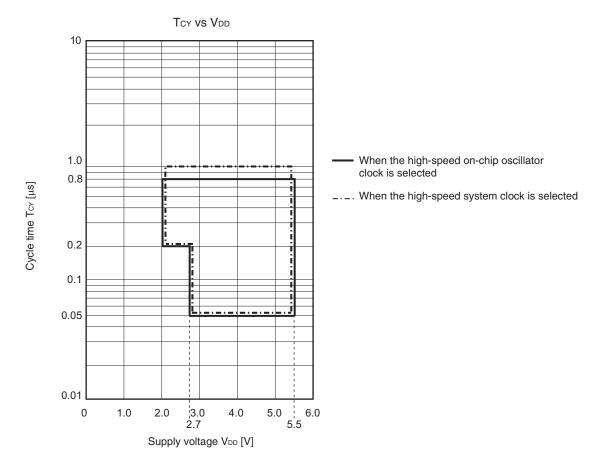
 $(T_A = -40 \text{ to } +85^{\circ}\text{C}, 2.0 \text{ V} \le \text{V}_{DD} \le 5.5 \text{ V}, \text{ V}_{SS} = 0 \text{ V})$

Items	Symbol	Condi	tions	MIN.	TYP.	MAX.	Unit
Instruction cycle (minimum	Тсч	When high-speed on-	$2.7~V \leq V_{\text{DD}} \leq 5.5~V$	0.05		0.8	μs
instruction execution time)		chip oscillator clock (fiH) is selected	$2.0~V \leq V_{\text{DD}} < 2.7~V$	0.2		0.8	μs
		When high-speed	$2.7~V \leq V_{\text{DD}} \leq 5.5~V$	0.05		1.0	μs
		system clock (fмx) is selected	$2.0~V \leq V_{\text{DD}} < 2.7~V$	0.2		1.0	μs
External system clock	External system clock T _{EX}		$2.7~V \leq V_{\text{DD}} \leq 5.5~V$	1.0		20	MHz
frequency			$2.0~V \leq V_{\text{DD}} < 2.7~V$	1.0		5	MHz
External system clock input	Texh, Texl		$2.7~V \leq V_{\text{DD}} \leq 5.5~V$	24			ns
high-level width, low-level width			$2.0~\text{V} \leq \text{V}_\text{DD} < 2.7~\text{V}$	95			ns
TI00 to TI03 input high-level width, low-level width	t⊤ıн, t⊤ı∟	Noise filter is not used		1/fмск + 10			ns
TO00 to TO03 output	fто	$4.0~V \leq V_{\text{DD}} \leq 5.5~V$				10	MHz
frequency		$2.7~V \leq V_{\text{DD}} < 4.0~V$				5	MHz
		$2.0~V \leq V_{\text{DD}} < 2.7~V$				2.5	MHz
PCLBUZ0 output frequency	f PCL	$4.0~V \leq V_{\text{DD}} \leq 5.5~V$				10	MHz
		$2.7 \text{ V} \leq \text{V}_{\text{DD}} < 4.0 \text{ V}$				5	MHz
		$2.0 \text{ V} \le \text{V}_{\text{DD}} < 2.7 \text{ V}$				2.5	MHz
RESET low-level width	t RSL			10			μs

Remark fmck: Timer array unit operation clock frequency

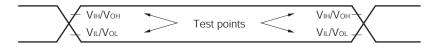
(Operation clock to be set by the timer clock select register 0 (TPS0) and the CKS0n1 bit of timer mode register 0nH (TMR0nH). n: Channel number (n = 0 to 3))



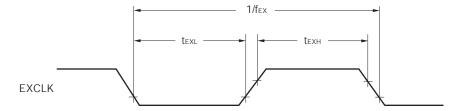


Minimum Instruction Execution Time during Main System Clock Operation

AC Timing Test Points



External System Clock Timing



Parameter	Symbol	(Conditions	MIN.	TYP.	MAX.	Unit
SCKp cycle time	tkCY1	tксү1 ≥ 4/fc∟к	$2.7~V \leq V_{\text{DD}} \leq 5.5~V$	200			ns
			$2.0~V \leq V_{\text{DD}} \leq 5.5~V$	800			ns
SCKp high-/low-level width	t кн1, t к∟1	$2.7 \text{ V} \leq \text{V}_{\text{DD}} \leq 5.5 \text{ V}$		tkcy1/2 - 18			ns
		$2.0 \text{ V} \leq V_{\text{DD}} \leq 5.5 \text{ V}$		tkcy1/2 - 50			ns
SIp setup time (to SCKp↑) Note 1	tsik1	$2.7 \text{ V} \leq V_{\text{DD}} \leq 5$.5 V	47			ns
		$2.0~V \le V_{\text{DD}} \le 5$.5 V	110			ns
SIp hold time (from SCKp↑) ^{Note 1}	tksi1			19			ns
Delay time from SCKp↓ to SOp output ^{Note 2}	tkso1	C = 30 pF ^{Note 3}				25	ns

(2) CSI mode (master mode, SCKp... internal clock output)

 $(T_A = -40 \text{ to } +85^{\circ}\text{C}, 2.0 \text{ V} \le \text{V}_{DD} \le 5.5 \text{ V}, \text{V}_{SS} = 0 \text{ V})$

Notes 1. When DAP0n = 0 and CKP0n = 0, or DAP0n = 1 and CKP0n = 1. The SIp setup time becomes "to SCKp↓" and SIp hold time becomes "from SCKp↓" when DAP0n = 0 and CKP0n = 1, or DAP0n = 1 and CKP0n = 0.

2. When DAP0n = 0 and CKP0n = 0, or DAP0n = 1 and CKP0n = 1. The delay time to SOp output becomes "from SCKp[↑]" when DAP0n = 0 and CKP0n = 1, or DAP0n = 1 and CKP0n = 0.

3. C is the load capacitance of the SCKp and SOp output lines.

(3) CSI mode (slave mode, SCKp... external clock input)

Parameter	Symbol	Conditions			MIN.	TYP.	MAX.	Unit
SCKp cycle time	t ксү2	$2.7 \text{ V} \le \text{V}_{\text{DD}} \le 5.5 \text{ V}$		< > 16 MHz	8/fмск			ns
			fмск	< ≤ 16 MHz	6/fмск			ns
		$2.0 \text{ V} \leq V_{\text{DD}} \leq 5.5 \text{ V}$		6/fмск			ns	
SCKp high-/low-level width	t кн2,	$2.0 \text{ V} \leq V_{\text{DD}} \leq 5.5 \text{ V}$		tксү2/2 - 18			ns	
	tĸ∟2							
SIp setup time (to SCKp↑) ^{Note 1}	tsik2	$2.7~V \le V_{\text{DD}} \le 5.5$	V		1/fмск+ 20			ns
		$2.0~V \leq V_{\text{DD}} \leq 5.5~V$			1/fмск+ 30			ns
SIp hold time (from SCKp^) $^{\rm Note \ 1}$	tksi2	$2.0 \text{ V} \le \text{V}_{\text{DD}} \le 5.5$	V		1/fмск+ 31			ns
Delay time from SCKp↓ to SOp output ^{Note 2}	tkso2	C = 30 pF Note 3	2.7 V ≤ \	$V_{DD} \le 5.5 \text{ V}$			2/fмск+50	ns
			2.0 V ≤ \	$V_{DD} \le 5.5 \text{ V}$			2/fмск+110	ns

$(T_A = -40 \text{ to } +85^{\circ}\text{C}, 2.0 \text{ V} \le \text{V}_{DD} \le 5.5 \text{ V}, \text{ V}_{SS} = 0 \text{ V})$

- Notes 1. When DAP0n = 0 and CKP0n = 0, or DAP0n = 1 and CKP0n = 1. The SIp setup time becomes "to SCKp↓" and the SIp hold time becomes "from SCKp↓" when DAP0n = 0 and CKP0n = 1, or DAP0n = 1 and CKP0n = 0.
 - 2. When DAP0n = 0 and CKP0n = 0, or DAP0n = 1 and CKP0n = 1. The delay time to SOp output becomes "from SCKp[↑]" when DAP0n = 0 and CKP0n = 1, or DAP0n = 1 and CKP0n = 0.
 - 3. C is the load capacitance of the SOp output lines.

Remarks 1. p: CSI number (p = 00, 01), n: Channel number (n = 0, 1)

 fMCK: Serial array unit operation clock frequency (Operation clock to be set by the serial clock select register 0 (SPS0) and the CKS0n bit of the serial mode register 0nH (SMR0nH). n: Channel number (n = 0, 1))

(4) Simplified I²C mode

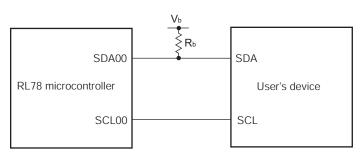
 $(T_A = -40 \text{ to } +85^{\circ}\text{C}, 2.0 \text{ V} \le \text{V}_{DD} \le 5.5 \text{ V}, \text{ V}_{SS} = 0 \text{ V})$

	/				
Parameter	Symbol	Conditions	MIN.	MAX.	Unit
SCLr clock frequency	fsc∟	C_{b} = 100 pF, R_{b} = 3 k Ω		400 Note 1	kHz
Hold time when SCLr = "L"	tLOW	C_{b} = 100 pF, R_{b} = 3 k Ω	1150		ns
Hold time when SCLr = "H"	tнigн	C_b = 100 pF, R_b = 3 k Ω	1150		ns
Data setup time (reception)	tsu: dat	C_b = 100 pF, R_b = 3 k Ω	1/fмск + 145 ^{Note 2}		ns
Data hold time (transmission)	thd: dat	C_b = 100 pF, R_b = 3 k Ω	0	355	ns

Notes 1. The value must also be equal to or less than $f_{MCK}/4$.

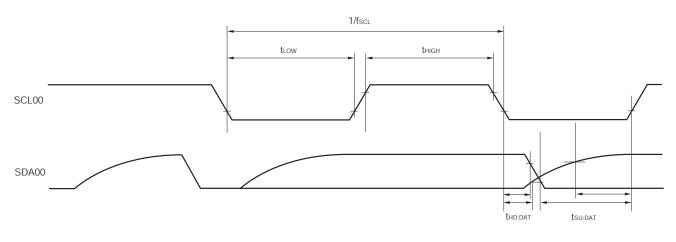
2. Set the fmck value to keep the hold time of SCLr = "L" and SCLr = "H".

Caution Select the N-ch open drain output (VDD tolerance) mode for the SDAr pin by using the port output mode register 0 (POM0).



Simplified I²C mode connection diagram

Simplified I²C mode serial transfer timing



Remarks 1. R_b [Ω]: Communication line (SDAr) pull-up resistance,

Cb [F]: Communication line (SCLr, SDAr) load capacitance

- 2. r: IIC number (r = 00)
- fMCK: Serial array unit operation clock frequency (Operation clock to be set by the serial clock select register 0 (SPS0) and the CKS0n bit of the serial mode register 0nH (SMR0nH). n: Channel number (n = 0))

RENESAS

2.6 Analog Characteristics

2.6.1 A/D converter characteristics

(Target pin: ANI0 to ANI6, internal reference voltage)

 $(T_A = -40 \text{ to } +85^{\circ}\text{C}, 2.4 \text{ V} \le \text{V}_{DD} \le 5.5 \text{ V}, \text{ V}_{SS} = 0 \text{ V})$

Parameter	Symbol	C	conditions	MIN.	TYP.	MAX.	Unit
Resolution	RES			8		10	bit
Overall error ^{Notes 1, 2, 3}	AINL	10-bit resolution	V _{DD} = 5 V		±1.7	±3.1	LSB
			V _{DD} = 3 V		±2.3	±4.5	LSB
Conversion time	t CONV	10-bit resolution	$2.7~V \leq V_{\text{DD}} \leq 5.5~V$	3.4		18.4	μs
		Target pin: ANI0 to ANI6	$2.4~V \leq V_{\text{DD}} \leq 5.5~V^{\text{ Note 5}}$	4.6		18.4	μs
		10-bit resolution Target pin: internal reference voltage ^{Note 6}	$2.4~V \leq V_{\text{DD}} \leq 5.5~V$	4.6		18.4	μs
Zero-scale error ^{Notes 1, 2, 3, 4}	Ezs	10-bit resolution	V _{DD} = 5 V			±0.19	%FSR
			V _{DD} = 3 V			±0.39	%FSR
Full-scale errorNotes 1, 2, 3, 4	Efs	10-bit resolution	V _{DD} = 5 V			±0.29	%FSR
			V _{DD} = 3 V			±0.42	%FSR
Integral linearity error ^{Notes 1, 2, 3}	ILE	10-bit resolution	V _{DD} = 5 V			±1.8	LSB
			V _{DD} = 3 V			±1.7	LSB
Differential linearity error	DLE	10-bit resolution	V _{DD} = 5 V			±1.4	LSB
Notes 1, 2, 3			V _{DD} = 3 V			±1.5	LSB
Analog input voltage	VAIN	Target pin: ANI0 to	ANI6	0		Vdd	V
		Target pin: internal	reference voltage Note 6		VREG Note 7		V

Notes 1. TYP. Value is the average value at $T_A = 25^{\circ}C$. MAX. value is the average value $\pm 3\sigma$ at normal distribution.

- 2. These values are the results of characteristic evaluation and are not checked for shipment.
- **3.** Excludes quantization error ($\pm 1/2$ LSB).
- 4. This value is indicated as a ratio (%FSR) to the full-scale value.
- Set the LV0 bit in the A/D converter mode register 0 (ADM0) to 0 when conversion is done in the operating voltage range of 2.4 V ≤ V_{DD} < 2.7 V.
- **6.** Set the LV0 bit in the A/D converter mode register 0 (ADM0) to 0 when the internal reference voltage is selected as the target for conversion.
- 7. Refer to 2.6.3 Internal reference voltage characteristics.
- Cautions 1. Arrange wiring and insert the capacitor so that no noise appears on the power supply/ground line.
 - 2. Do not allow any pulses that rapidly change such as digital signals to be input/output to/from the pins adjacent to the conversion pin during A/D conversion.
 - 3. Note that the internal reference voltage cannot be used as the reference voltage of the comparator when the internal reference voltage is selected as the target for A/D conversion.

2.6.2 Comparator characteristics

Parameter	Symbol	Conditions		MIN.	TYP.	MAX.	Unit
Input voltage range	IVREF	IVREF0 pin input (when C0VFR bit = 0)		0		Vdd - 1.4	V
		Internal reference voltage (when C0VRF bit = 1) ^{Note 1}			VREG Note 2		V
	IVCMP	IVCMP0 pin input		-0.3		VDD + 0.3	V
Output delay	td	VDD = 3.0 V,	High-speed mode			0.5	μs
		input slew rate > 50 mV/µs	Low-speed mode		2.0		μs
Operation stabilization wait time	tсмр			100			μs

- **Notes 1.** When the internal reference voltage is selected as the reference voltage of the comparator, the internal reference voltage cannot be used as the target for A/D conversion.
 - 2. Refer to 2.6.3 Internal reference voltage characteristics.

2.6.3 Internal reference voltage characteristics

$(T_A = -40 \text{ to } +85^{\circ}\text{C}, 2.0 \text{ V} \le \text{V}_{DD} \le 5.5 \text{ V}, \text{ V}_{SS} = 0 \text{ V})$

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Internal reference voltage	VREG		0.74	0.815	0.89	V
Operation stabilization wait time	tamp	When A/D converter is used (ADS register = 07H)	5			μs

Note The internal reference voltage cannot be simultaneously used by the A/D converter and the comparator; only one of them must be selected.



2.8 Flash Memory Programming Characteristics

$(T_A = 0 \text{ to } + 40^{\circ}C, 4.5 \text{ V} \le V_{DD} \le 5.5 \text{ V}, \text{ Vss} = 0 \text{ V})$

Parameter	Symbol	Conditions		MIN.	TYP.	MAX.	Unit
Code flash memory rewritable times Notes 1, 2, 3	Cerwr	Retained for 20 years.	T _A = +85°C	1000			Times

- **Notes 1.** 1 erase + 1 write after the erase is regarded as 1 rewrite. The retaining years are until next rewrite after the rewrite.
 - 2. When using flash memory programmer.
 - **3.** These are the characteristics of the flash memory and the results obtained from reliability testing by Renesas Electronics Corporation.

2.9 Dedicated Flash Memory Programmer Communication (UART)

 $(T_A = 0 \text{ to } + 40^{\circ}\text{C}, 4.5 \text{ V} \le \text{V}_{DD} \le 5.5 \text{ V}, \text{V}_{SS} = 0 \text{ V})$

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Transfer rate				115,200		bps

Remark The transfer rate during flash memory programming is fixed to 115,200 bps.



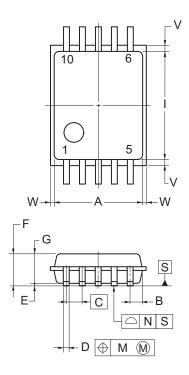
3. PACKAGE DRAWINGS

3.1 10-pin products

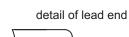
<R>

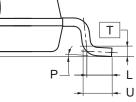
R5F10Y17ASP, R5F10Y16ASP, R5F10Y14ASP R5F10Y17DSP, R5F10Y16DSP, R5F10Y14DSP

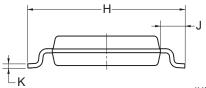
JEITA Package Code	RENESAS Code	Previous Code	MASS (TYP.) [g]
P-LSSOP10-4.4x3.6-0.65	PLSP0010JA-A	P10MA-65-CAC-2	0.05



Each lead centerline is located within 0.13 mm of its true position (T.P.) at maximum material







(UNIT:mm)

ITEM	DIMENSIONS
А	3.60±0.10
В	0.50
С	0.65 (T.P.)
D	0.24 ± 0.08
E	0.10 ± 0.05
F	1.45 MAX.
G	1.20 ± 0.10
Н	6.40 ± 0.20
I	4.40±0.10
J	1.00 ± 0.20
К	$0.17^{+0.08}_{-0.07}$
L	0.50
М	0.13
N	0.10
Р	$3^{\circ}{+5^{\circ}}_{-3^{\circ}}$
Т	0.25 (T.P.)
U	0.60 ± 0.15
V	0.25 MAX.
W	0.15 MAX.

©2012 Renesas Electronics Corporation. All rights reserved.

NOTE

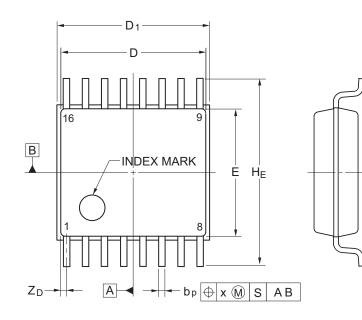
condition.

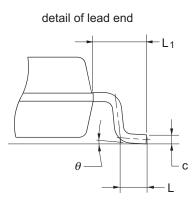


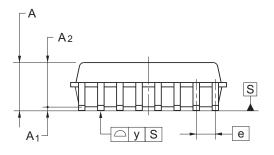
3.2 16-pin products

R5F10Y47ASP, R5F10Y46ASP, R5F10Y44ASP<R>R5F10Y47DSP, R5F10Y46DSP, R5F10Y44DSP

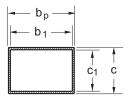
JEITA Package code	RENESAS code	Previous code	MASS(TYP.)[g]
P-SSOP16-4.4x5-0.65	PRSP0016JC-B	P16MA-65-FAB-1	0.08







Terminal cross section



Referance	Dimens	sion in Mil	lillimeters		
Symbol	Min	Nom	Max		
D	4.85	5.00	5.15		
D ₁	5.05	5.20	5.35		
E	4.20	4.40	4.60		
A ₂		1.50			
A ₁	0.075	0.125	0.175		
A		_	1.725		
bp	0.17	0.24	0.32		
b ₁		0.22			
с	0.14	0.17	0.20		
C ₁		0.15			
θ	0°		8°		
HE	6.20	6.40	6.60		
е		0.65			
х			0.13		
У			0.10		
Z _D		0.225			
L	0.35	0.50	0.65		
L ₁		1.00			



Revision History

RL78/G10 Datasheet

			Description
Rev.	Date	Page	Summary
1.00	Apr 15, 2013	-	First Edition issued
2.00	Jan 10, 2014	1, 2	Modification of descriptions in 1.1 Features
		3	Modification of description in 1.2 List of Part Numbers
		4	Modification of remark 2 in 1.3.1 10-pin products and 1.3.2 16-pin products
		8, 9	Addition of description of R5F10Y17ASP in 1.6 Outline of Functions
		11	Modification of description in 2.1 Absolute Maximum Ratings
		12	Modification of description in 2.2 Oscillator Characteristics
		13, 14	Modification of description, notes 1 to 4, and caution in 2.3.1 Pin
		40	characteristics
		16	Addition of description, notes 1 to 6, and remarks 1 and 2 in (2) Flash ROM: 4 KB of 10-pin products, and 16-pin products
		17	Addition of description, notes 1 to 6, and remarks 1 to 3 in (3) Peripheral
		17	Functions (Common to all products)
		18	Modification of description in 2.4 AC Characteristics
		19	Addition of figure of Minimum Instruction Execution Time during Main System
		15	Clock Operation
		19	Addition of figure of External System Clock Timing
		20	Modification of TI/TO Timing
		25	Addition of description in 2.5.2 Serial interface IICA
		26	Modification of description and notes 1 to 6 in 2.6.1 A/D converter
			characteristics
		27	Addition of description, notes 1 and 2 in 2.6.2 Comparator characteristics
		27	Addition of description and note in 2.6.3 Internal reference voltage
			characteristics
		28	Addition of caution in 2.6.4 SPOR Circuit characteristics
		28	Addition of figure in 2.6.6 Data retention power supply voltage characteristics
		31	Addition of R5F10Y17ASP in 3.1 10-pin products
		32	Modification of package drawing in 3.2 16-pin products
3.00	Nov 19, 2014	3	Addition of industrial applications in Figure 1-1 Part Number, Memory Size, and Package of RL78/G10
		3	Addition of industrial applications in Table 1-1 List of Ordering Part Numbers
		4	Addition of description to pin configuration in 1.3.1 10-pin products and 1.3.2
		-	16-pin products
		22	Correction of error in 2.5.1 Serial array unit, (3) CSI mode (slave mode,
			SCKp external clock input)
		28	Renamed to 2.7 RAM Data Retention Characteristics and modification of figure
		31	Addition of industrial application in 3.1 10-pin products
		32	Addition of industrial application in 3.2 16-pin products and modification of
			package drawing
3.10	Aug 12, 2016	1	Addition of description to Rich Analog in 1.1 Features
		3	Corrected Table 1-1. List of Ordering Part Numbers
		4	Modification of 1.3 Pin Configuration (Top View)
		31, 32	Deletion of under development

All trademarks and registered trademarks are the property of their respective owners.

SuperFlash is a registered trademark of Silicon Storage Technology, Inc. in several countries including the United States and Japan.

Caution: This product uses SuperFlash® technology licensed from Silicon Storage Technology, Inc.

NOTES FOR CMOS DEVICES

- (1) VOLTAGE APPLICATION WAVEFORM AT INPUT PIN: Waveform distortion due to input noise or a reflected wave may cause malfunction. If the input of the CMOS device stays in the area between VIL (MAX) and VIH (MIN) due to noise, etc., the device may malfunction. Take care to prevent chattering noise from entering the device when the input level is fixed, and also in the transition period when the input level passes through the area between VIL (MAX) and VIH (MIN).
- (2) HANDLING OF UNUSED INPUT PINS: Unconnected CMOS device inputs can be cause of malfunction. If an input pin is unconnected, it is possible that an internal input level may be generated due to noise, etc., causing malfunction. CMOS devices behave differently than Bipolar or NMOS devices. Input levels of CMOS devices must be fixed high or low by using pull-up or pull-down circuitry. Each unused pin should be connected to VDD or GND via a resistor if there is a possibility that it will be an output pin. All handling related to unused pins must be judged separately for each device and according to related specifications governing the device.
- (3) PRECAUTION AGAINST ESD: A strong electric field, when exposed to a MOS device, can cause destruction of the gate oxide and ultimately degrade the device operation. Steps must be taken to stop generation of static electricity as much as possible, and quickly dissipate it when it has occurred. Environmental control must be adequate. When it is dry, a humidifier should be used. It is recommended to avoid using insulators that easily build up static electricity. Semiconductor devices must be stored and transported in an anti-static container, static shielding bag or conductive material. All test and measurement tools including work benches and floors should be grounded. The operator should be grounded using a wrist strap. Semiconductor devices must not be touched with bare hands. Similar precautions need to be taken for PW boards with mounted semiconductor devices.
- (4) STATUS BEFORE INITIALIZATION: Power-on does not necessarily define the initial status of a MOS device. Immediately after the power source is turned ON, devices with reset functions have not yet been initialized. Hence, power-on does not guarantee output pin levels, I/O settings or contents of registers. A device is not initialized until the reset signal is received. A reset operation must be executed immediately after power-on for devices with reset functions.
- (5) POWER ON/OFF SEQUENCE: In the case of a device that uses different power supplies for the internal operation and external interface, as a rule, switch on the external power supply after switching on the internal power supply. When switching the power supply off, as a rule, switch off the external power supply and then the internal power supply. Use of the reverse power on/off sequences may result in the application of an overvoltage to the internal elements of the device, causing malfunction and degradation of internal elements due to the passage of an abnormal current. The correct power on/off sequence must be judged separately for each device and according to related specifications governing the device.
- (6) INPUT OF SIGNAL DURING POWER OFF STATE : Do not input signals or an I/O pull-up power supply while the device is not powered. The current injection that results from input of such a signal or I/O pull-up power supply may cause malfunction and the abnormal current that passes in the device at this time may cause degradation of internal elements. Input of signals during the power off state must be judged separately for each device and according to related specifications governing the device.

Notice 1. Descriptions of circuits, software and other related information in this document are provided only to illustrate the operation of semiconductor products and application examples. You are fully responsible for the incorporation of these circuits, software, and information in the design of your equipment. Renesas Electronics assumes no responsibility for any losses incurred by you or third parties arising from the use of these circuits software or information 2. Renesas Electronics has used reasonable care in preparing the information included in this document, but Renesas Electronics does not warrant that such information is error free. Renesas Electronics assumes no liability whatsoever for any damages incurred by you resulting from errors in or omissions from the information included herein 3. Renesas Electronics does not assume any liability for infringement of patents, copyrights, or other intellectual property rights of third parties by or arising from the use of Renesas Electronics products or technical information described in this document. No license, express, implied or otherwise, is granted hereby under any patents, copyrights or other intellectual property rights of Renesas Electronics or 4. You should not alter, modify, copy, or otherwise misappropriate any Renesas Electronics product, whether in whole or in part. Renesas Electronics assumes no responsibility for any losses incurred by you or third parties arising from such alteration, modification, copy or otherwise misappropriation of Renesas Electronics product. 5. Renesas Electronics products are classified according to the following two quality grades: "Standard" and "High Quality". The recommended applications for each Renesas Electronics product depends on the product's quality grade, as indicated below "Standard": Computers; office equipment; communications equipment; test and measurement equipment; audio and visual equipment; home electronic appliances; machine tools; personal electronic equipment; and industrial robots etc. "High Quality": Transportation equipment (automobiles, trains, ships, etc.); traffic control systems; anti-disaster systems; anti-crime systems; and safety equipment etc. Renesas Electronics products are neither intended nor authorized for use in products or systems that may pose a direct threat to human life or bodily injury (artificial life support devices or systems, surgical implantations etc.), or may cause serious property damages (nuclear reactor control systems, military equipment etc.). You must check the quality grade of each Renesas Electronics product before using it in a particular application. You may not use any Renesas Electronics product for any application for which it is not intended. Renesas Electronics shall not be in any way liable for any damages or losses incurred by you or third parties arising from the use of any Renesas Electronics product for which the product is not intended by Renesas Electronics. 6. You should use the Renesas Electronics products described in this document within the range specified by Renesas Electronics, especially with respect to the maximum rating, operating supply voltage range, movement power voltage range, heat radiation characteristics, installation and other product characteristics. Renesas Electronics shall have no liability for malfunctions or damages arising out of the use of Renesas Electronics products beyond such specified ranges 7. Although Renesas Electronics endeavors to improve the quality and reliability of its products, semiconductor products have specific characteristics such as the occurrence of failure at a certain rate and malfunctions under certain use conditions. Further, Renesas Electronics products are not subject to radiation resistance design. Please be sure to implement safety measures to guard them against the possibility of physical injury, and injury or damage caused by fire in the event of the failure of a Renesas Electronics product, such as safety design for hardware and software including but not limited to redundancy, fire control and malfunction prevention, appropriate treatment for aging degradation or any other appropriate measures. Because the evaluation of microcomputer software alone is very difficult, lease evaluate the safety of the final products or systems manufactured by you 8. Please contact a Renesas Electronics sales office for details as to environmental matters such as the environmental compatibility of each Renesas Electronics product. Please use Renesas Electronics products in compliance with all applicable laws and regulations that regulate the inclusion or use of controlled substances, including without limitation, the EU RoHS Directive. Renesas Electronics assumes no liability for damages or losses occurring as a result of your noncompliance with applicable laws and regulations. 9. Renesas Electronics products and technology may not be used for or incorporated into any products or systems whose manufacture, use, or sale is prohibited under any applicable domestic or foreign laws or regulations. You should not use Renesas Electronics products or technology described in this document for any purpose relating to military applications or use by the military, including but not limited to the development of weapons of mass destruction. When exporting the Renesas Electronics products or technology described in this document, you should comply with the applicable export control laws and regulations and follow the procedures required by such laws and regulations 10. It is the responsibility of the buyer or distributor of Renesas Electronics products, who distributes, disposes of, or otherwise places the product with a third party, to notify such third party in advance of the contents and conditions set forth in this document, Renesas Electronics assumes no responsibility for any losses incurred by you or third parties as a result of unauthorized use of Renesas Electronics

products.

11. This document may not be reproduced or duplicated in any form, in whole or in part, without prior written consent of Renesas Electronics.

- 12. Please contact a Renesas Electronics sales office if you have any questions regarding the information contained in this document or Renesas Electronics products, or if you have any other inquiries.
- (Note 1) "Renesas Electronics" as used in this document means Renesas Electronics Corporation and also includes its majority-owned subsidiaries.

(Note 2) "Renesas Electronics product(s)" means any product developed or manufactured by or for Renesas Electronics.

Refer to "http://www.renesas.com/" for the latest and detailed information.

RENESAS

SALES OFFICES

Renesas Electronics Corporation

http://www.renesas.com

Renesas Electronics America Inc. 2801 Scott Boulevard Santa Clara, CA 95050-2549, U.S.A. Tel: +1-408-588-6000, Fax: +1-408-588-6130 Renesas Electronics Canada Limited 9251 Yonge Street, Suite 8309 Richmond Hill, Ontario Canada L4C 9T3 Tel: +1-905-237-2004 **Renesas Electronics Europe Limited** Dukes Meadow, Millboard Road, Bourne End, Buckinghamshire, SL8 5FH, U.K Tel: +44-1628-585-100, Fax: +44-1628-585-900 Renesas Electronics Europe GmbH Arcadiastrasse 10, 40472 Düsseldorf, German Tel: +49-211-6503-0, Fax: +49-211-6503-1327 Renesas Electronics (China) Co., Ltd. Room 1709, Quantum Plaza, No.27 ZhiChunLu Haidian District, Beijing 100191, P.R.China Tel: +88-10-8235-1155, Fax: +88-10-8235-7679 Renesas Electronics (Shanghai) Co., Ltd. Unit 301, Tower A, Central Towers, 555 Langao Road, Putuo District, Shanghai, P. R. China 200333 Tei: +86-21-2226-0888, Fax: +86-21-2226-0999 Renesas Electronics Hong Kong Limited Non-sease Lectronics nong round Limited Unit 1601-1611, 16/F., Tower 2, Grand Century Place, 193 Prince Edward Road West, Mongkok, Kowloon, Hong Kong Tel: +852-2265-6688, Fax: +852 2886-9022 Renesas Electronics Taiwan Co., Ltd. 13F, No. 363, Fu Shing North Road, Taipei 10543, Taiwan Tel: +886-2-8175-9600, Fax: +886 2-8175-9670 Renesas Electronics Singapore Pte. Ltd. 80 Bendemeer Road, Unit #06-02 Hyflux Innovation Centre, Singapore 339949 Tel: +55-631-30200, Fax: +65-6213-0300 1207, Block B, Menara Amcorp, Amcorp Trade Centre, No. 18, Jln Persiaran Barat, 46050 Petaling Jaya, Selangor Darul Ehsan, Malaysia +60-3-7955-9390, Fax: +60-3-7955-9510 Renesas Electronics Malaysia Sdn.Bhd. Unit 1207. Block B. Menara Amcorp. Amco Renesas Electronics India Pvt. Ltd. No.777C, 100 Feet Road, HAL II Stage, Indiranagar, Bangalore, India Tel: +91-80-67208700, Fax: +91-80-67208777 Renesas Electronics Korea Co., Ltd. 12F., 234 Teheran-ro, Gangnam-Gu, Seoul, 135-080, Korea Tel: +82-2-558-3737, Fax: +82-2-558-5141